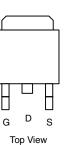
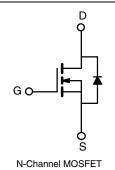


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0035				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.0039				
I _D (A)	120				
Configuration	Single				

TO-263





FEATURES

- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % $\rm R_g$ and UIS Tested
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ORDERING INFORMATION				
Package	TO-263			
Lead (Pb)-free and Halogen-free	SQM120N06-3m5L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage		V _{DS}	60	N/		
Gate-Source Voltage		V _{GS}	± 20	V		
Continuous Drain Currenta	T _C = 25 °C	- I _D -	120			
Continuous Drain Current"	T _C = 125 °C		120			
Continuous Source Current (Diode Conduction) ^a	I _S	120	А			
Pulsed Drain Current ^b	I _{DM}	480				
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	100			
Single Pulse Avalanche Energy		E _{AS}	500	mJ		
Mauianan Davian Diasia atianh	T _C = 25 °C	D	375	W		
Maximum Power Dissipation ^b	T _C = 125 °C	P _D	125	vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)		R _{thJC}	0.4	0/10		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

SQM120N06-3m5L



Vishay Siliconix

PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static					•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		2.0	2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	900		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	120	-	-	А	
		$V_{GS} = 10 V$	I _D = 30 A	-	0.0028	0.0035		
Drain-Source On-State Resistance ^a	Р	$V_{GS} = 10 V$	$I_D = 30 \text{ A}, \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	-	0.0064		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0080	Ω	
		$V_{GS} = 4.5 V$	I _D = 20 A	-	0.0031	0.0039		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		-	190	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	11 755	14 700	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	1112	1400		
Reverse Transfer Capacitance	C _{rss}			-	481	605		
Total Gate Charge ^c	Qg			-	220	330	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 110 \text{ A}$	-	35	-		
Gate-Drain Charge ^c	Q _{gd}			-	35	-		
Gate Resistance	R _g	f = 1 MHz		0.6	1.3	2	Ω	
Turn-On Delay Time ^c	t _{d(on)}				19	29		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD}=30~\text{V},~\text{R}_{\text{L}}=0.27~\Omega\\ \text{I}_{\text{D}}\cong110~\text{A},~\text{V}_{\text{GEN}}=10~\text{V},~\text{R}_{\text{g}}=2.5~\Omega \end{array}$		-	23	35	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	83	125		
Fall Time ^c	t _f			-	35	53		
Source-Drain Diode Ratings and Char	acteristics ^b				•			
Pulsed Current ^a	I _{SM}			-	-	480	Α	
Forward Voltage	V _{SD}	I _F :	= 50 A, V _{GS} = 0	-	0.8	1.5	V	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

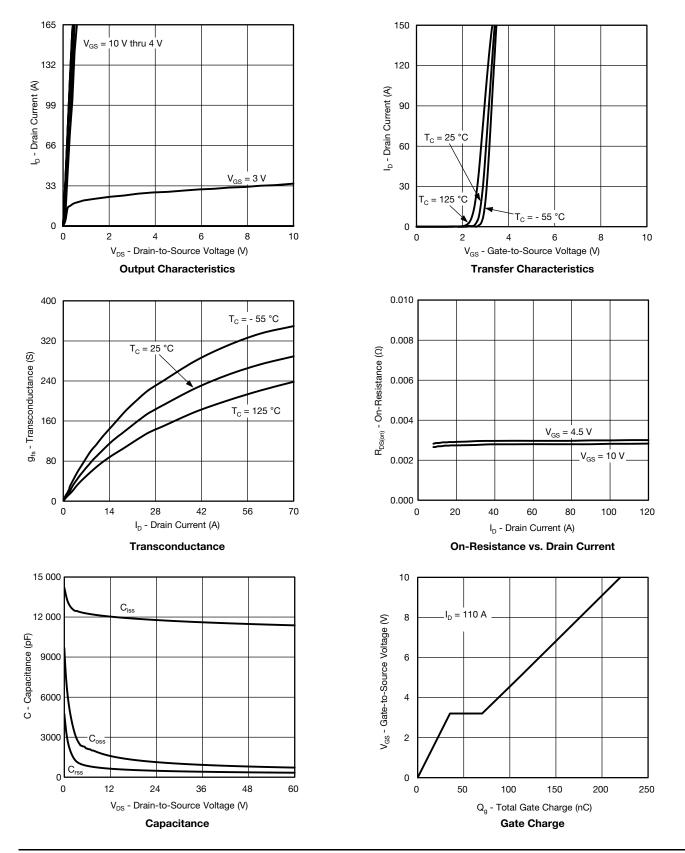
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



S13-2117-Rev. A, 07-Oct-13

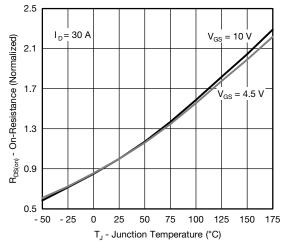
3

Document Number: 63814

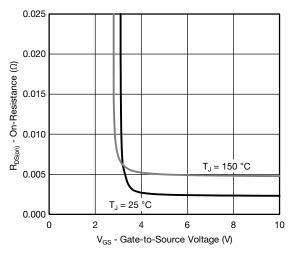
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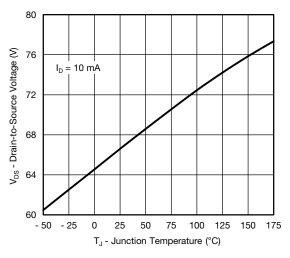
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)







On-Resistance vs. Gate-to-Source Voltage

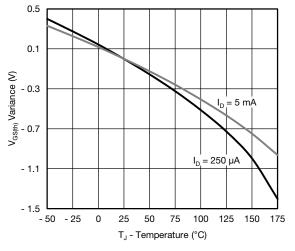


Drain Source Breakdown vs. Junction Temperature

T_J = 150 10 I_s - Source Current (A) 1 T_J = 25 °C 0.1 0.01 0.001 0.0 0.2 0.4 0.6 0.8 1.0 1.2 V_{SD} - Source-to-Drain Voltage (V)

100

Source Drain Diode Forward Voltage



Threshold Voltage

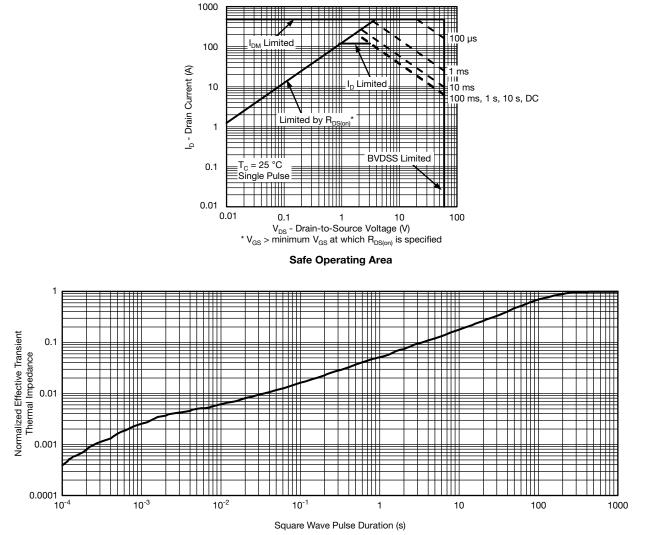
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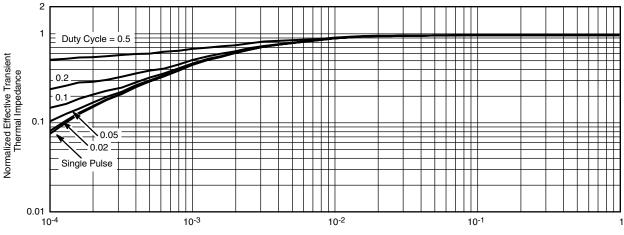
THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63814.



D²PAK / TO-263 and TO-262

Ordering codes for the SQ rugged series power MOSFETs in the D²PAK / TO-263 and TO-262 packages:

DATASHEET PART NUMBER	OLD ORDERING CODE ^a	NEW ORDERING CODE
SQM100N04-2m7	SQM100N04-2M7-GE3	SQM100N04-2M7_GE3
SQM100N10-10	SQM100N10-10-GE3	SQM100N10-10_GE3
SQM110N05-06L	SQM110N05-06L-GE3	SQM110N05-06L_GE3
SQM110P06-8m9L	SQM110P06-8M9L-GE3	SQM110P06-8M9L_GE3
SQM120N02-1m3L	SQM120N02-1M3L-GE3	SQM120N02-1M3L_GE3
SQM120N03-1m5L	SQM120N03-1M5L-GE3	SQM120N03-1M5L_GE3
SQM120N04-1m7	SQM120N04-1M7-GE3	SQM120N04-1M7_GE3
SQM120N04-1m7L	SQM120N04-1M7L-GE3	SQM120N04-1M7L_GE3
SQM120N04-1m9	SQM120N04-1M9-GE3	SQM120N04-1M9_GE3
SQM120N06-06	SQM120N06-06-GE3	SQM120N06-06_GE3
SQM120N06-3m5L	SQM120N06-3M5L-GE3	SQM120N06-3M5L_GE3
SQM120N10-09	SQM120N10-09-GE3	SQM120N10-09_GE3
SQM120N10-3m8	SQM120N10-3M8-GE3	SQM120N10-3M8_GE3
SQM120P04-04L	SQM120P04-04L-GE3	SQM120P04-04L_GE3
SQM120P06-07L	SQM120P06-07L-GE3	SQM120P06-07L_GE3
SQM200N04-1m1L	SQM200N04-1M1L-GE3	SQM200N04-1M1L_GE3
SQM200N04-1m7L	SQM200N04-1M7L-GE3	SQM200N04-1M7L_GE3
SQM200N04-1m8	SQM200N04-1M8-GE3	SQM200N04-1M8_GE3
SQM25N15-52	SQM25N15-52-GE3	SQM25N15-52_GE3
SQM35N30-97	SQM35N30-97-GE3	SQM35N30-97_GE3
SQM40N10-30	SQM40N10-30-GE3	SQM40N10-30_GE3
SQM40N15-38	SQM40N15-38-GE3	SQM40N15-38_GE3
SQM40P10-40L	SQM40P10-40L-GE3	SQM40P10-40L_GE3
SQM47N10-24L	SQM47N10-24L-GE3	SQM47N10-24L_GE3
SQM50020EL	-	SQM50020EL_GE3
SQM50N04-4m0L	SQM50N04-4M0L-GE3	SQM50N04-4M0L_GE3
SQM50N04-4m1	SQM50N04-4M1-GE3	SQM50N04-4M1_GE3
SQM50P03-07	SQM50P03-07-GE3	SQM50P03-07_GE3
SQM50P04-09L	SQM50P04-09L-GE3	SQM50P04-09L_GE3
SQM50P06-15L	SQM50P06-15L-GE3	SQM50P06-15L_GE3
SQM50P08-25L	SQM50P08-25L-GE3	SQM50P08-25L_GE3
SQM60N06-15	SQM60N06-15-GE3	SQM60N06-15_GE3
SQM60N20-35	SQM60N20-35-GE3	SQM60N20-35_GE3
SQM85N15-19	SQM85N15-19-GE3	SQM85N15-19_GE3
SQV120N10-3m8	SQV120N10-3m8-GE3	SQV120N10-3m8_GE3
SQV120N06-4m7L	-	SQV120N06-4m7L_GE3

Note

a. Old ordering code is obsolete and no longer valid for new orders



TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
	А	0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
с*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	E	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
	е	0.100	BSC	2.54 BSC		
	К	0.045	0.055	1.143	1.397	
	L	0.575	0.625	14.605	15.875	
	L1	0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 % of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
 - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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